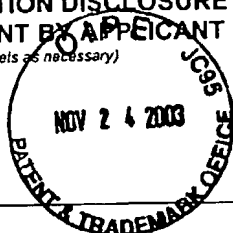


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STATEMENT BY APPLICANT**
(Use as many sheets as necessary)



Complete if Known

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First Named Inventor Ahn, Kie
Group Art Unit 1756
Examiner Name Duda, Kathleen

Attorney Docket No: 1303.016US1

Sheet 1 of 1

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